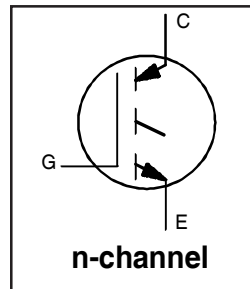


IRG4PC30WPbF

INSULATED GATE BIPOLAR TRANSISTOR

Features

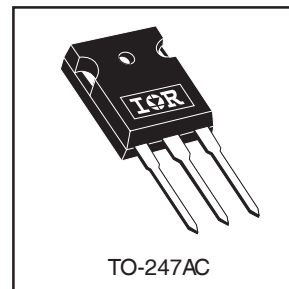
- Designed expressly for Switch-Mode Power Supply and PFC (power factor correction) applications
- Industry-benchmark switching losses improve efficiency of all power supply topologies
- 50% reduction of Eoff parameter
- Low IGBT conduction losses
- Latest-generation IGBT design and construction offers tighter parameters distribution, exceptional reliability
- Lead-Free



| |
|-----------------------------|
| $V_{CES} = 600V$ |
| $V_{CE(on) max.} = 2.70V$ |
| @ $V_{GE} = 15V, I_C = 12A$ |

Benefits

- Lower switching losses allow more cost-effective operation than power MOSFETs up to 150 kHz ("hard switched" mode)
- Of particular benefit to single-ended converters and boost PFC topologies 150W and higher
- Low conduction losses and minimal minority-carrier recombination make these an excellent option for resonant mode switching as well (up to >>300 kHz)



Absolute Maximum Ratings

| | Parameter | Max. | Units |
|---------------------------|--|--------------------|-------|
| V_{CES} | Collector-to-Emitter Breakdown Voltage | 600 | V |
| $I_C @ T_C = 25^\circ C$ | Continuous Collector Current | 23 | A |
| $I_C @ T_C = 100^\circ C$ | Continuous Collector Current | 12 | |
| I_{CM} | Pulsed Collector Current ① | 92 | |
| I_{LM} | Clamped Inductive Load Current ② | 92 | |
| V_{GE} | Gate-to-Emitter Voltage | ± 20 | V |
| E_{ARV} | Reverse Voltage Avalanche Energy ③ | 180 | mJ |
| $P_D @ T_C = 25^\circ C$ | Maximum Power Dissipation | 100 | W |
| $P_D @ T_C = 100^\circ C$ | Maximum Power Dissipation | 42 | |
| T_J | Operating Junction and Storage Temperature Range | -55 to + 150 | °C |
| T_{STG} | | | |
| | | | |
| | Mounting torque, 6-32 or M3 screw. | 10 lbf·in (1.1N·m) | |

Thermal Resistance

| | Parameter | Typ. | Max. | Units |
|-----------------|---|----------|------|--------|
| $R_{\theta JC}$ | Junction-to-Case | --- | 1.2 | °C/W |
| $R_{\theta CS}$ | Case-to-Sink, Flat, Greased Surface | 0.24 | --- | |
| $R_{\theta JA}$ | Junction-to-Ambient, typical socket mount | --- | 40 | |
| Wt | Weight | 6 (0.21) | --- | g (oz) |

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|---------------------------------|--|------|------|-----------|----------------------|--|
| $V_{(BR)CES}$ | Collector-to-Emitter Breakdown Voltage | 600 | — | — | V | $V_{GE} = 0V, I_C = 250\mu A$ |
| $V_{(BR)ECS}$ | Emitter-to-Collector Breakdown Voltage ④ | 18 | — | — | V | $V_{GE} = 0V, I_C = 1.0A$ |
| $\Delta V_{(BR)CES}/\Delta T_J$ | Temperature Coeff. of Breakdown Voltage | — | 0.34 | — | V/ $^\circ\text{C}$ | $V_{GE} = 0V, I_C = 1.0mA$ |
| $V_{CE(ON)}$ | Collector-to-Emitter Saturation Voltage | — | 2.1 | 2.7 | V | $I_C = 12A$ $V_{GE} = 15V$ See Fig.2, 5 |
| | | — | 2.45 | — | | |
| | | — | 1.95 | — | | |
| $V_{GE(th)}$ | Gate Threshold Voltage | 3.0 | — | 6.0 | | $V_{CE} = V_{GE}, I_C = 250\mu A$ |
| $\Delta V_{GE(th)}/\Delta T_J$ | Temperature Coeff. of Threshold Voltage | — | -11 | — | mV/ $^\circ\text{C}$ | $V_{CE} = V_{GE}, I_C = 250\mu A$ |
| g_{fe} | Forward Transconductance ⑤ | 11 | 16 | — | S | $V_{CE} = 100V, I_C = 12A$ |
| I_{CES} | Zero Gate Voltage Collector Current | — | — | 250 | μA | $V_{GE} = 0V, V_{CE} = 600V$ $V_{GE} = 0V, V_{CE} = 10V, T_J = 25^\circ\text{C}$ $V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$ |
| | | — | — | 2.0 | | |
| | | — | — | 1000 | | |
| I_{GES} | Gate-to-Emitter Leakage Current | — | — | ± 100 | nA | $V_{GE} = \pm 20V$ |

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|--------------|-----------------------------------|------|------|------|-------|---|
| Q_g | Total Gate Charge (turn-on) | — | 51 | 76 | nC | $I_C = 12A$ $V_{CC} = 400V$ $V_{GE} = 15V$ See Fig.8 |
| Q_{ge} | Gate - Emitter Charge (turn-on) | — | 7.6 | 11 | | |
| Q_{gc} | Gate - Collector Charge (turn-on) | — | 18 | 27 | | |
| $t_{d(on)}$ | Turn-On Delay Time | — | 25 | — | ns | $T_J = 25^\circ\text{C}$ $I_C = 12A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 23\Omega$ Energy losses include "tail" See Fig. 10, 11, 13, 14 |
| t_r | Rise Time | — | 16 | — | | |
| $t_{d(off)}$ | Turn-Off Delay Time | — | 99 | 150 | | |
| t_f | Fall Time | — | 67 | 100 | | |
| E_{on} | Turn-On Switching Loss | — | 0.13 | — | mJ | See Fig. 10, 11, 13, 14 |
| E_{off} | Turn-Off Switching Loss | — | 0.13 | — | | |
| E_{ts} | Total Switching Loss | — | 0.26 | 0.35 | | |
| $t_{d(on)}$ | Turn-On Delay Time | — | 24 | — | ns | $T_J = 150^\circ\text{C}$, $I_C = 12A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 23\Omega$ Energy losses include "tail" See Fig. 13, 14 |
| t_r | Rise Time | — | 17 | — | | |
| $t_{d(off)}$ | Turn-Off Delay Time | — | 150 | — | | |
| t_f | Fall Time | — | 150 | — | | |
| E_{ts} | Total Switching Loss | — | 0.55 | — | mJ | |
| L_E | Internal Emitter Inductance | — | 13 | — | nH | Measured 5mm from package |
| C_{ies} | Input Capacitance | — | 980 | — | pF | $V_{GE} = 0V$ $V_{CC} = 30V$ $f = 1.0MHz$ See Fig. 7 |
| C_{oes} | Output Capacitance | — | 71 | — | | |
| C_{res} | Reverse Transfer Capacitance | — | 18 | — | | |

Notes:

- ① Repetitive rating; $V_{GE} = 20V$, pulse width limited by max. junction temperature. (See fig. 13b)
- ② $V_{CC} = 80\%(V_{CES}), V_{GE} = 20V, L = 10\mu H, R_G = 23\Omega$, (See fig. 13a)
- ③ Repetitive rating; pulse width limited by maximum junction temperature.
- ④ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.
- ⑤ Pulse width $5.0\mu s$, single shot.

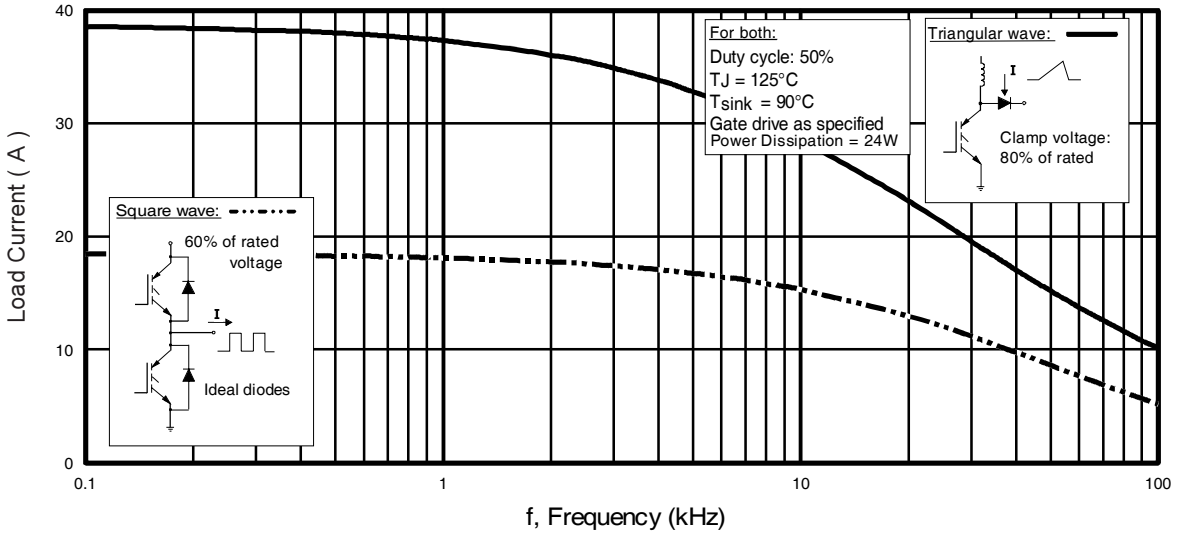


Fig. 1 - Typical Load Current vs. Frequency
(For square wave, $I = I_{RMS}$ of fundamental; for triangular wave, $I = I_{PK}$)

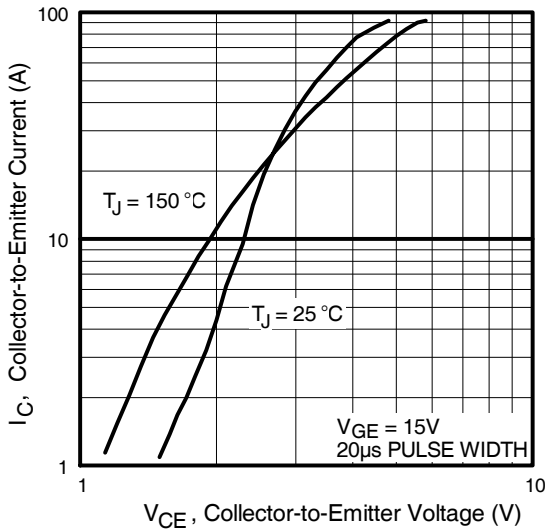


Fig. 2 - Typical Output Characteristics

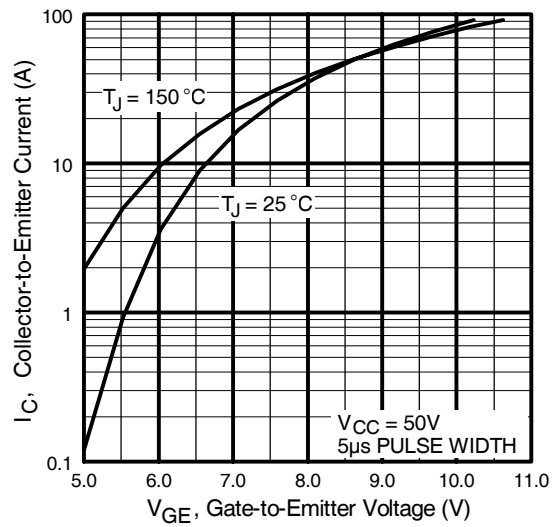


Fig. 3 - Typical Transfer Characteristics



Fig. 4 - Maximum Collector Current vs. Case Temperature

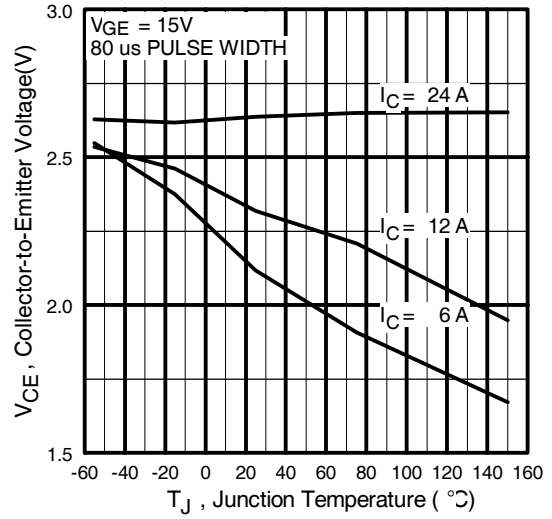


Fig. 5 - Collector-to-Emitter Voltage vs. Junction Temperature

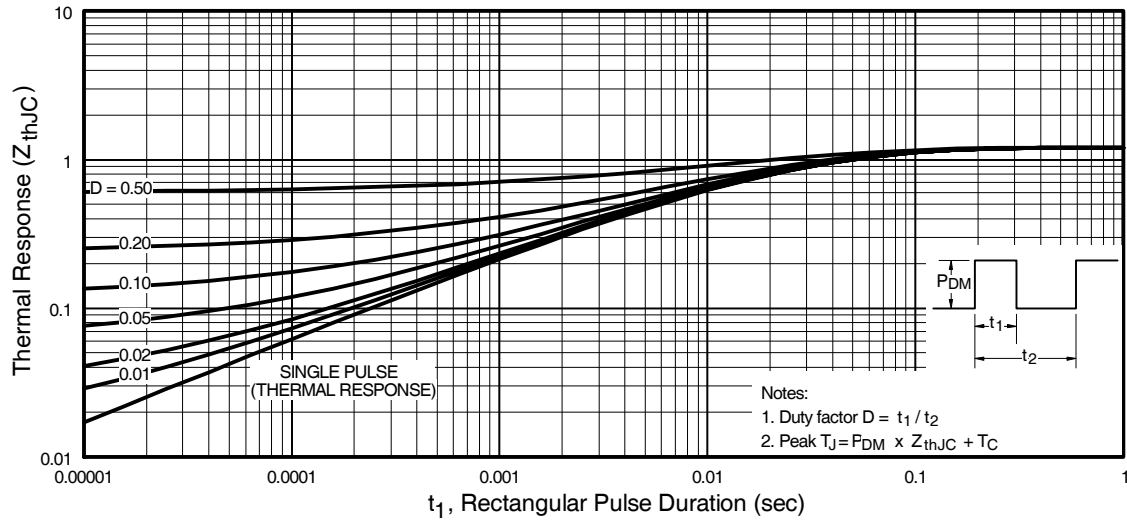


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

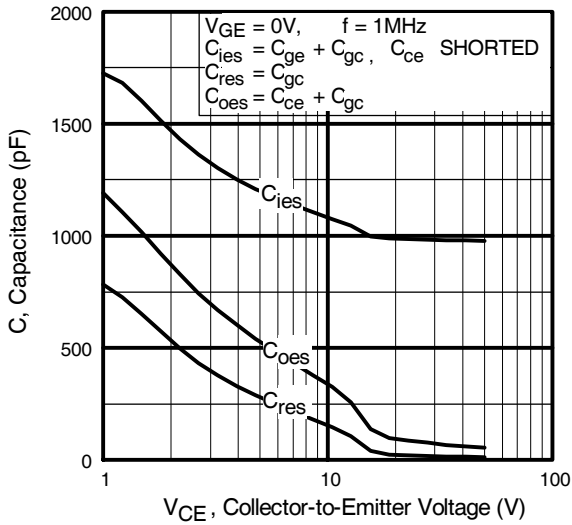


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

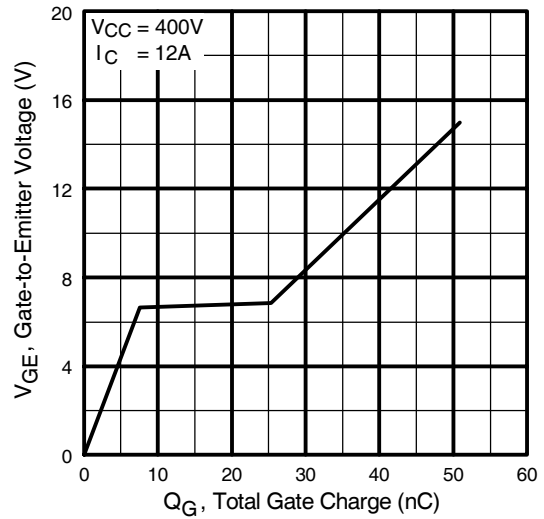


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

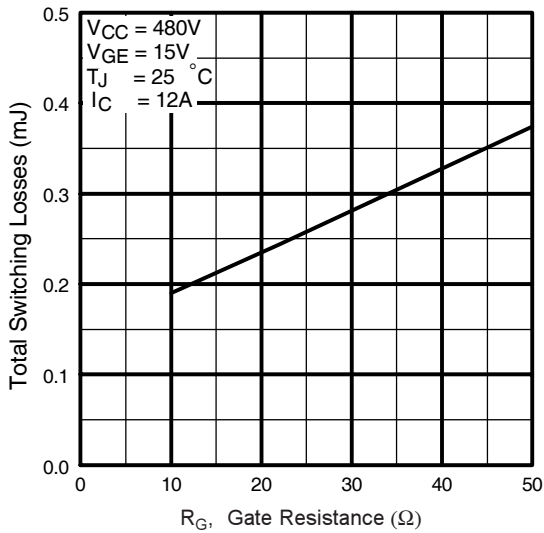


Fig. 9 - Typical Switching Losses vs. Gate Resistance

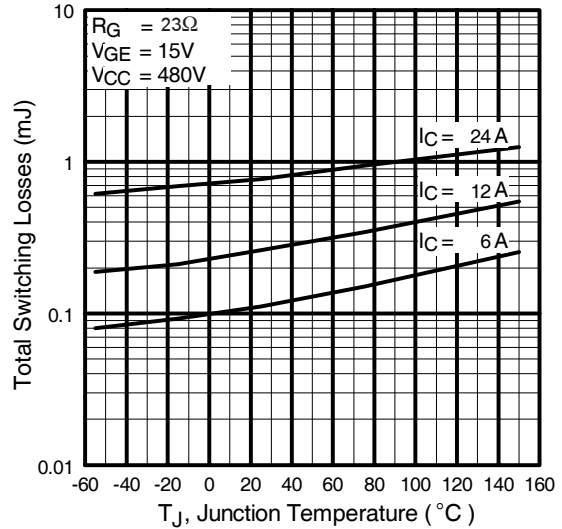


Fig. 10 - Typical Switching Losses vs. Junction Temperature

IRG4PC30WPbF

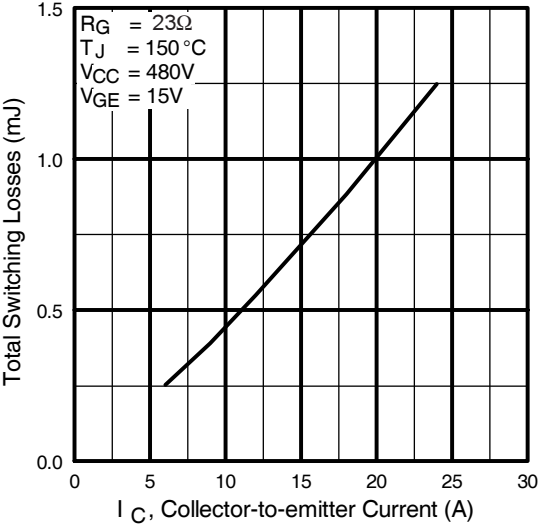


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

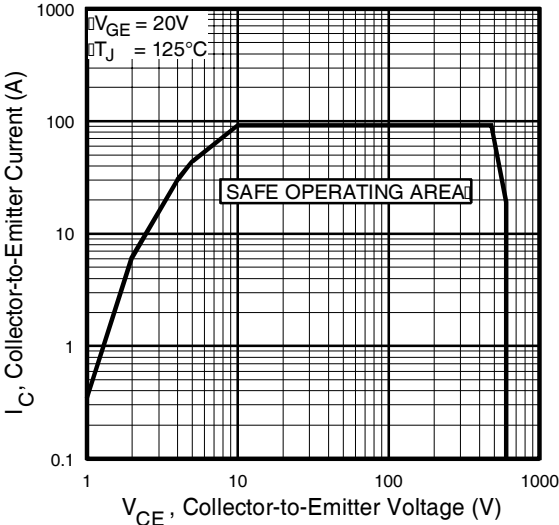
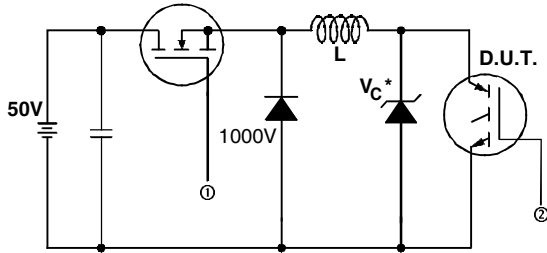


Fig. 12 - Turn-Off SOA



* Driver same type as D.U.T.; $V_c = 80\%$ of $V_{ce(max)}$
 * Note: Due to the 50V power supply, pulse width and inductor will increase to obtain rated I_d .

Fig. 13a - Clamped Inductive Load Test Circuit

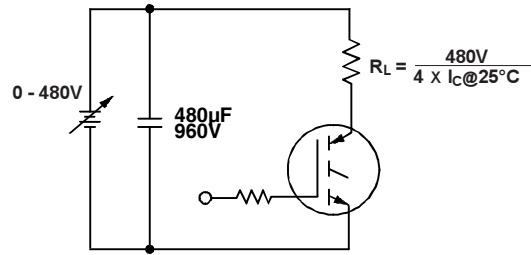


Fig. 13b - Pulsed Collector Current Test Circuit



Fig. 14a - Switching Loss Test Circuit

* Driver same type as D.U.T., $V_C = 480V$

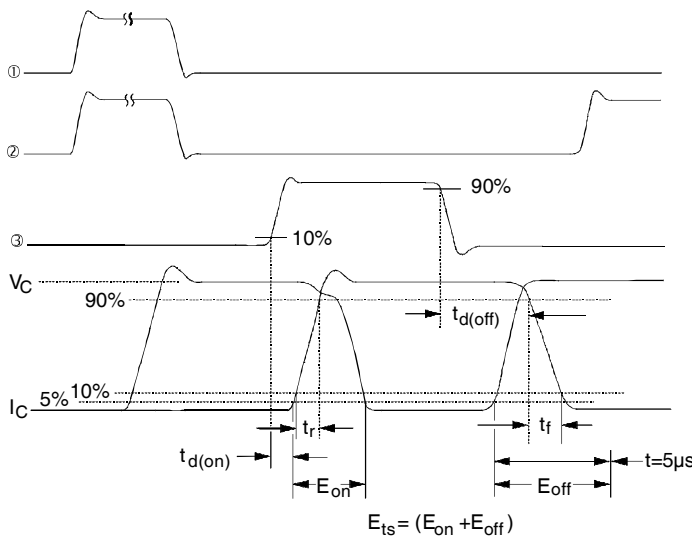


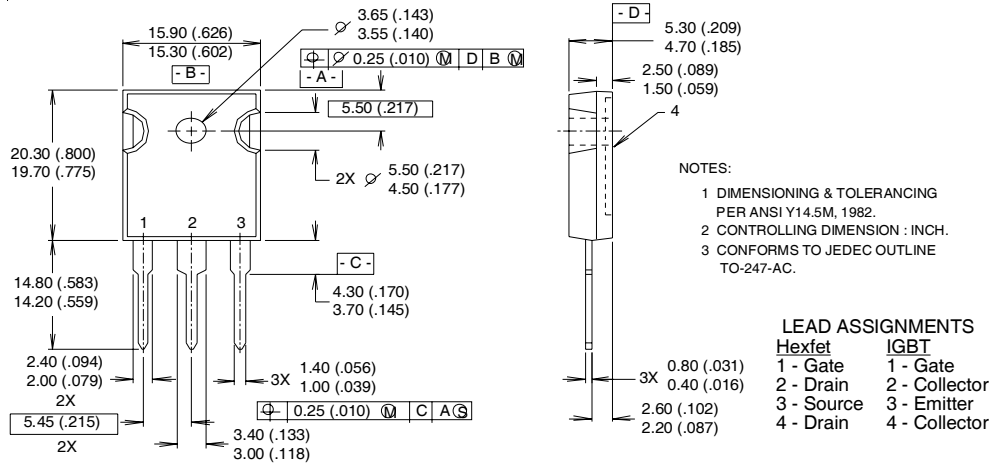
Fig. 14b - Switching Loss Waveforms

IRG4PC30WPbF

International
IR Rectifier

TO-247AC Package Outline

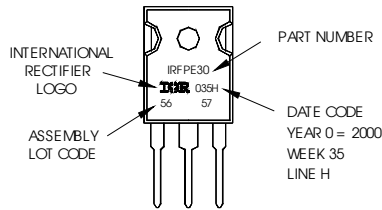
Dimensions are shown in millimeters (inches)



TO-247AC Part Marking Information

EXAMPLE: THIS IS AN IRFPE30
WITH ASSEMBLY
LOT CODE 5667
ASSEMBLED ON WW 35, 2000
IN THE ASSEMBLY LINE "H"

Note: "P" in assembly line
position indicates "Lead-Free"



Data and specifications subject to change without notice.

International
IR Rectifier

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TAC Fax: (310) 252-7903
Visit us at www.irf.com for sales contact information.12/03

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>